

N-Channel CICLON NexFET™ Power MOSFETs CSD16409Q3

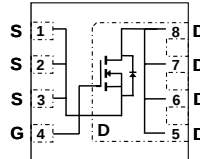


Features

- Ultra Low Qg & Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free



QFN 3.3mm x 3.3mm Plastic Package



Top View

Product Summary

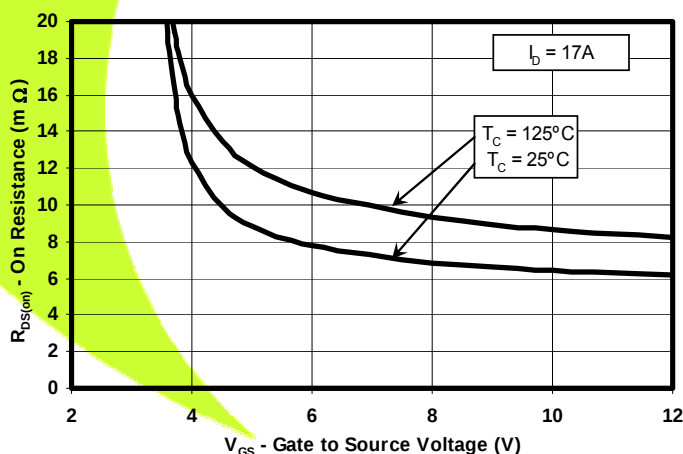
V_{DS}	25	V
Q_g	4.0	nC
Q_{gd}	1.0	nC
$R_{DS(on)}$	$V_{GS}=4.5V$	9.5 mΩ
	$V_{GS}=10V$	6.2 mΩ
V_{th}	2.0	V

Maximum Values ($T_A=25^\circ\text{C}$ unless otherwise stated)

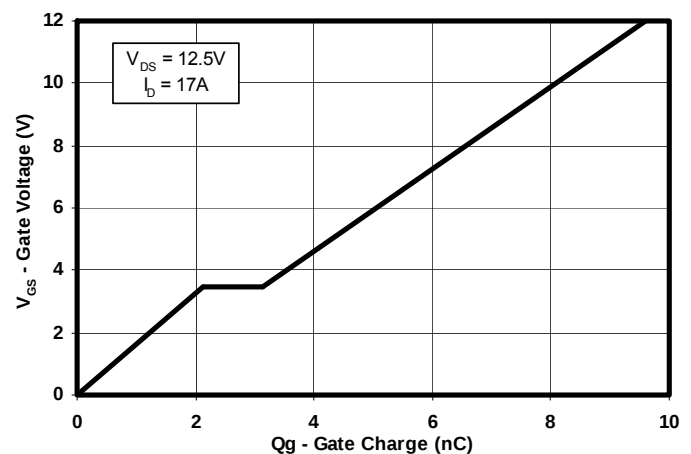
Symbol	Parameter	Value	Units
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+16 / -12	V
I_D	Continuous Drain Current, $T_C = 25^\circ\text{C}$	60	A
	Continuous Drain Current ¹	15	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ ²	90	A
P_D	Power Dissipation ¹	2.6	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Avalanche Energy, single pulse $I_D=38\text{A}$, $L = 0.1\text{mH}$, $R_G = 25\Omega$	72	mJ

1. $R_{\theta JA} = 47^\circ\text{C/W}$ on 1in^2 Cu (2 oz.) on 0.060" thick FR4 PCB.
2. Pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

$R_{DS(on)}$ vs. V_{GS}



Gate Charge



Ordering Information

Type	Package	Package Media	Qty	Ship
CSD16409Q3	QFN 3.3 X 3.3 Plastic Package	13 inch reel	2500	Tape and Reel

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Electrical Characteristics ($T_A = 25^{\circ}\text{C}$ unless otherwise stated)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
BV _{DSS}	Drain to Source Voltage	V _{GS} = 0V, I _D = 250μA	25	—	—	V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 20V	—	—	1	μA
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = +16/-12V	—	—	100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.7	2.0	2.3	V
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V, I _D = 17A	—	9.5	12.4	mΩ
		V _{GS} = 10V, I _D = 17A	—	6.2	8.2	mΩ
g _{fs}	Transconductance	V _{DS} = 15V, I _D = 17A	—	38	—	S
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V, V _{DS} = 12.5V f = 1MHz	—	600	800	pF
C _{OSS}	Output Capacitance		—	480	635	pF
C _{RSS}	Reverse Transfer Capacitance		—	40	55	pF
R _g	Series Gate Resistance		—	0.6	—	Ω
Q _g	Gate Charge Total (4.5V)	V _{DS} = 12.5V, I _D = 17A	—	4.0	5.6	nC
Q _{gd}	Gate Charge Gate to Drain		—	1.0	—	nC
Q _{gs}	Gate Charge Gate to Source		—	2.1	—	nC
Q _{g(th)}	Gate Charge at V _{th}		—	1.1	—	nC
Q _{OSS}	Output Charge	V _{DS} = 12.9V, V _{GS} = 0V	—	9.1	—	nC
t _{d(on)}	Turn On Delay Time	V _{DS} = 12.5V V _{GS} = 4.5V I _D = 17A R _G = 11 Ω	—	10	—	ns
t _r	Rise Time		—	30	—	ns
t _{d(off)}	Turn Off Delay Time		—	8	—	ns
t _f	Fall Time		—	10	—	ns
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _S = 17A, V _{GS} = 0V	—	0.85	1.0	V
Q _{rr}	Reverse Recovery Charge	V _{dd} =12.9V, I _F = 17A, di/dt = 300A/μs	—	13.8	—	nC
t _{rr}	Reverse Recovery Time	V _{dd} =12.9V, I _F = 17A, di/dt = 300A/μs	—	17.5	—	ns

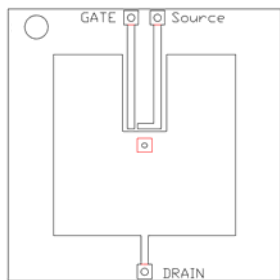
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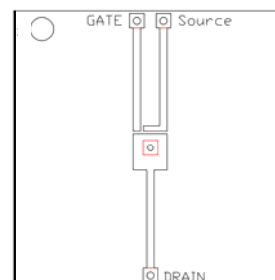
Thermal Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Units
Thermal Characteristics					
$R_{\theta JC}$	Thermal Resistance Junction to Case ³	—	—	3.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ^{3,4}	—	—	59	$^\circ\text{C/W}$

- $R_{\theta JC}$ is determined with the device mounted on a 1in square 2 oz. Cu pad on a 1.5x1.5 in .060in thick FR4 board. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
- Device mounted on FR4 Material with 1in² of 2 oz. Cu.



Max $R_{\theta JA} = 59^\circ\text{C/W}$ when
mounted on 1in² of
2 oz. Cu.



Max $R_{\theta JA} = 157^\circ\text{C/W}$ when
mounted on min pad area of
2 oz. Cu.

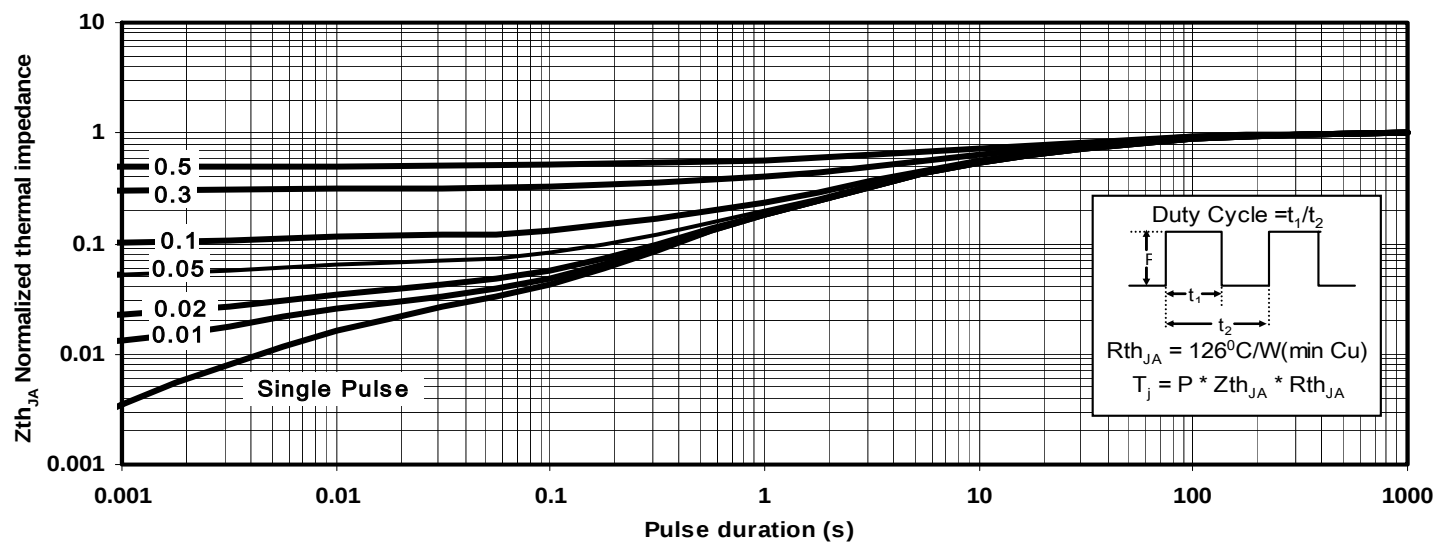


Figure 1: Transient Thermal Impedance

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Typical MOSFET Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise stated)

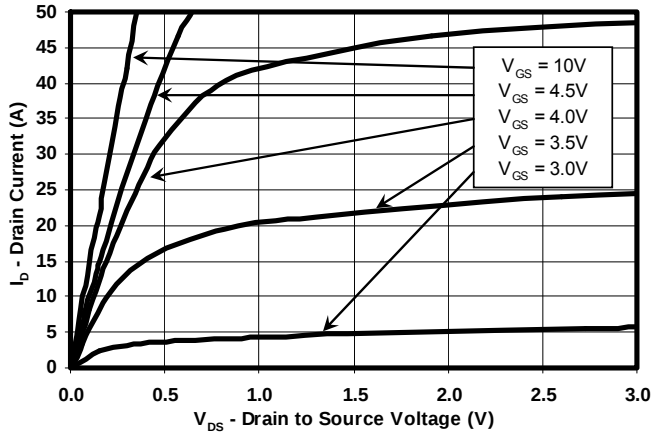


Figure 2: Saturation Characteristics

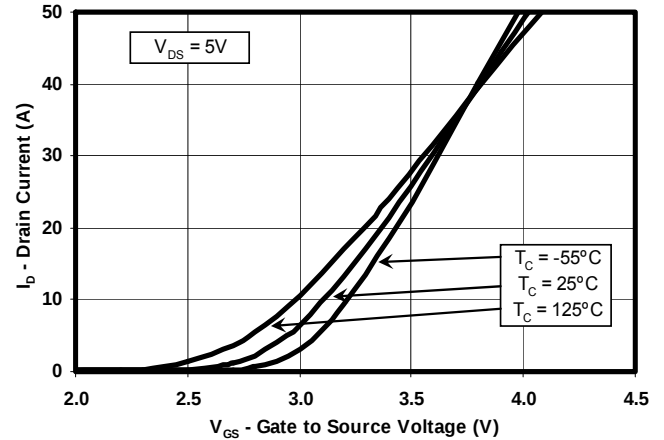


Figure 3: Transfer Characteristics

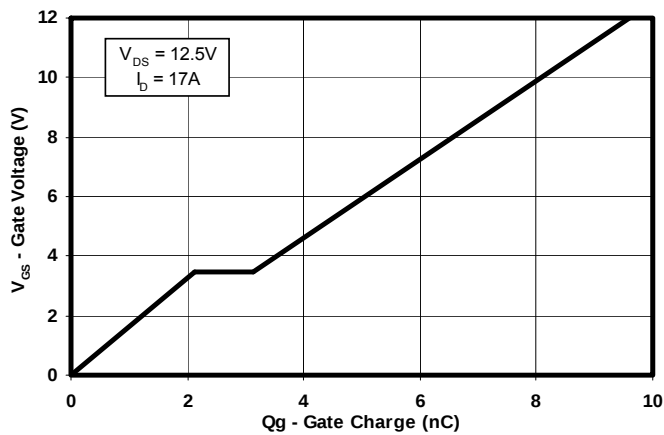


Figure 4: Gate Charge

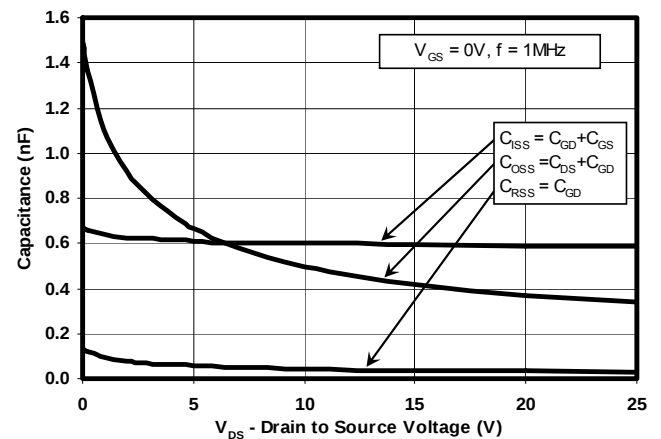


Figure 5: Capacitance

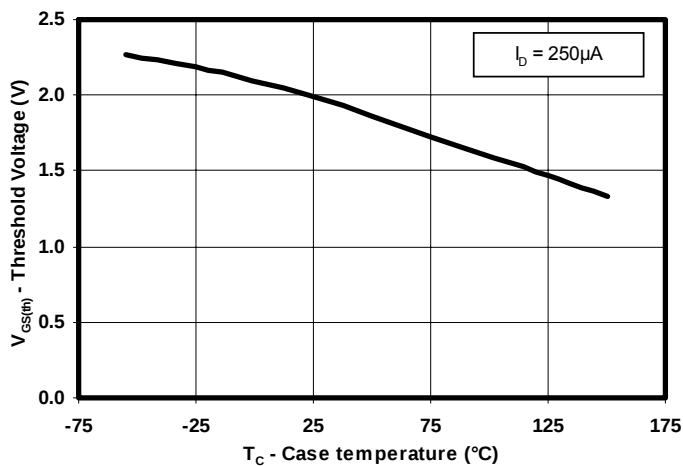


Figure 6: Threshold Voltage vs. Temperature

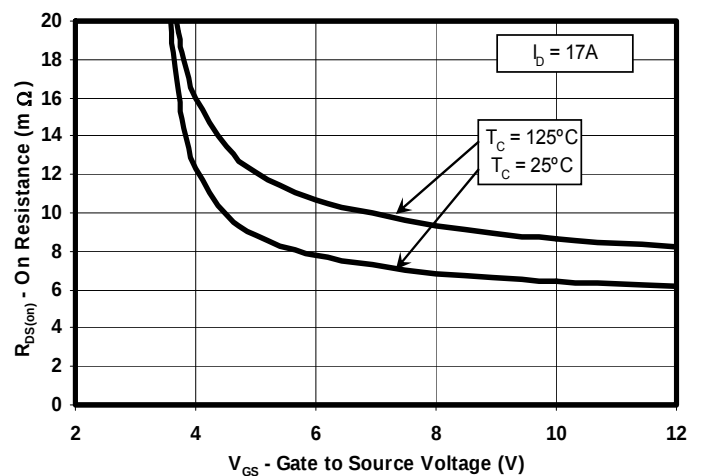


Figure 7: On Resistance vs. Gate Voltage

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Typical MOSFET Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise stated)

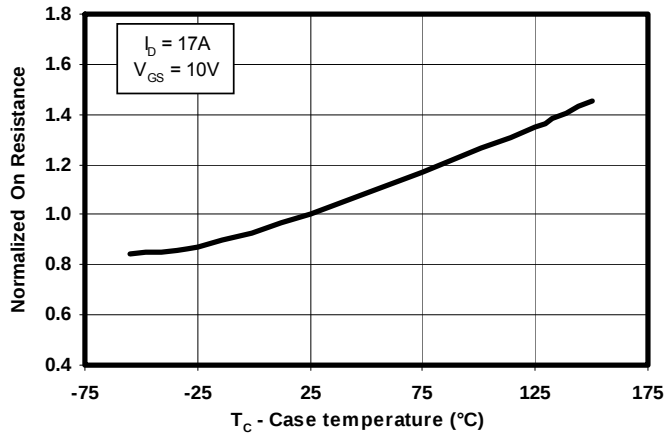


Figure 8: On Resistance vs. Temperature

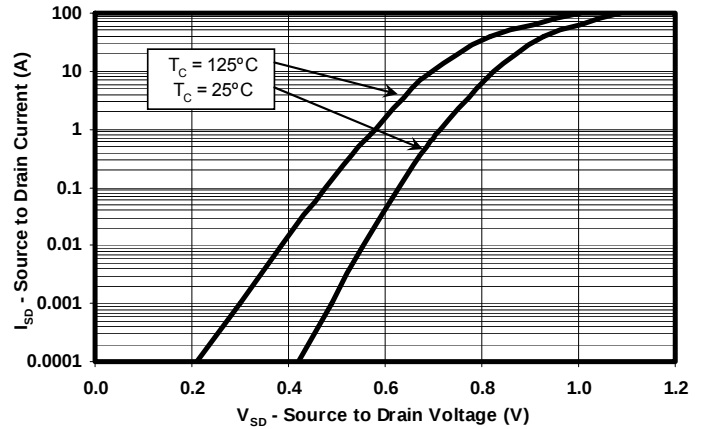


Figure 9: Typical Diode Forward Voltage

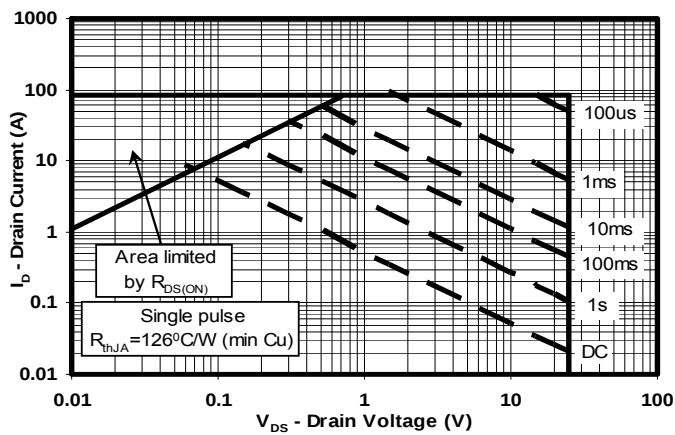


Figure 10: Maximum Safe Operating Area

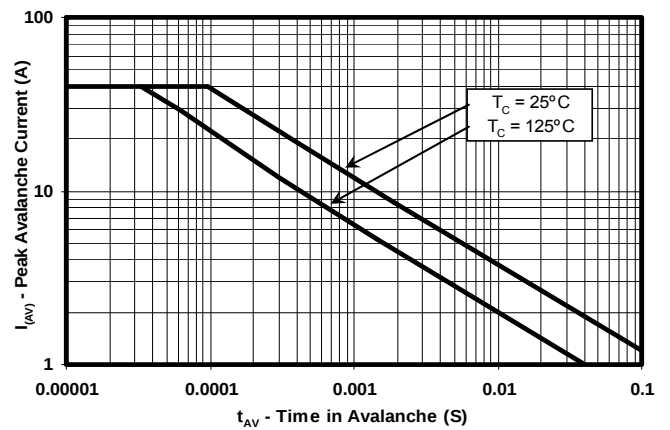


Figure 11: Single Pulse Unclamped Inductive Switching

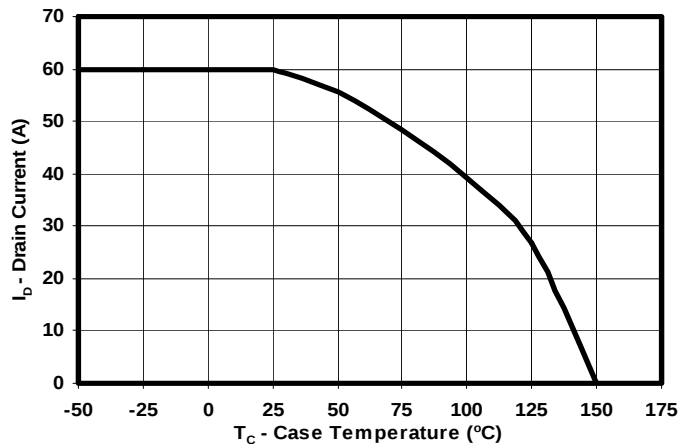
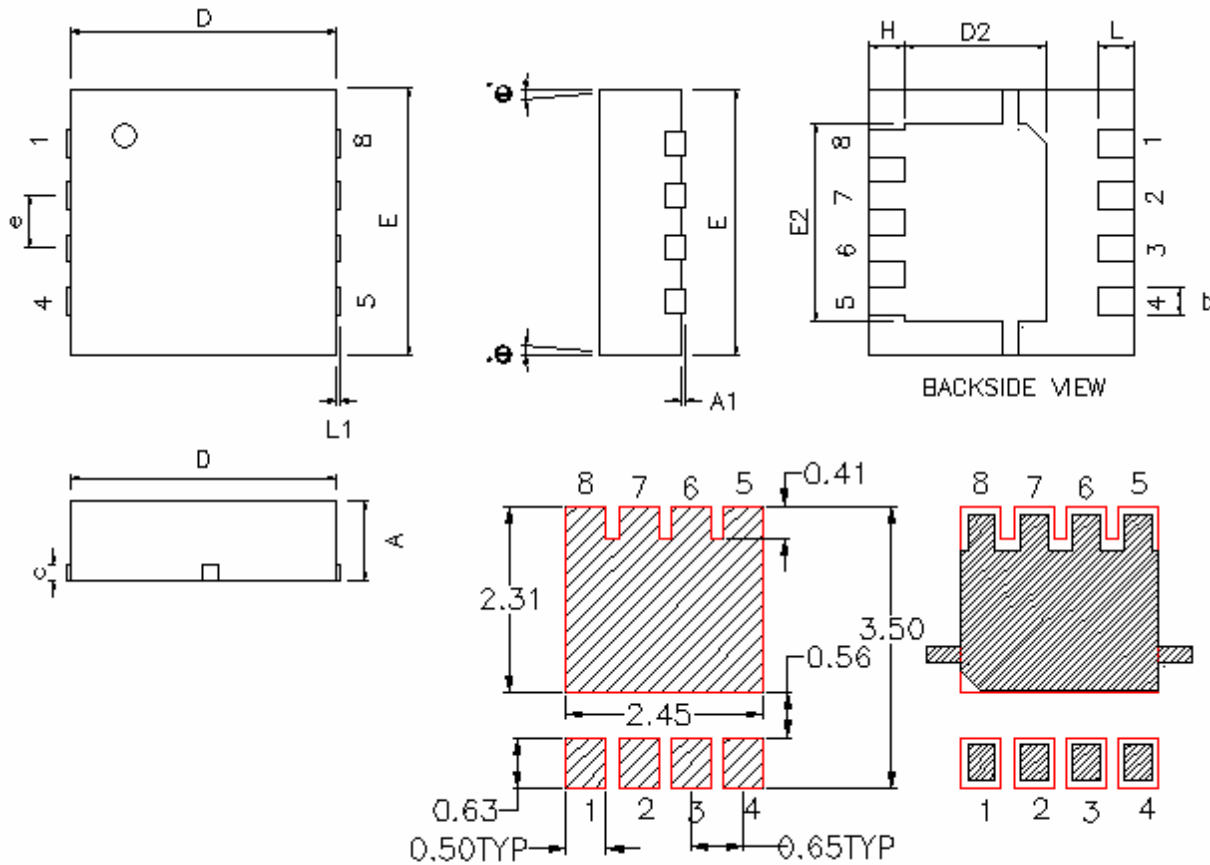


Figure 12: Maximum Drain Current vs. Temperature

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CSD16406Q3 Package Dimensions



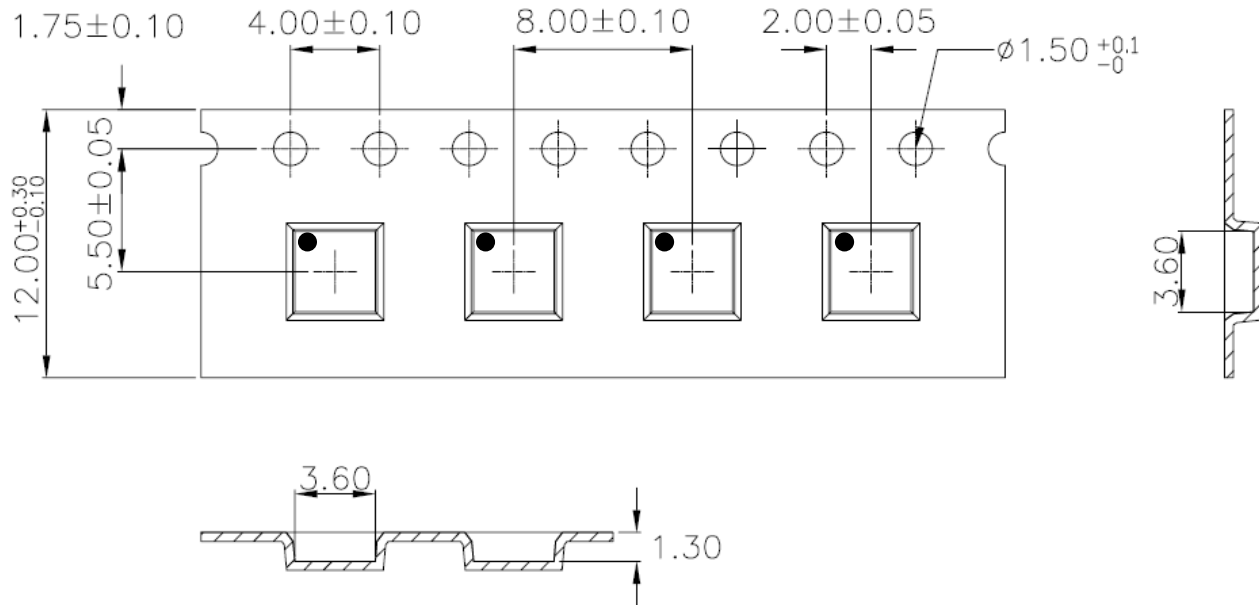
RECOMMENDED PCB LAND PATTERN

DIM	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.950	1.000	1.100	0.037	0.039	0.043
A1	0.000	0.000	0.050	0.000	0.000	0.002
b	0.280	0.340	0.400	0.011	0.013	0.016
c	0.150	0.200	0.250	0.006	0.008	0.010
D	3.200	3.300	3.400	0.126	0.130	0.134
D1	-	-	-	-	-	-
D2	1.650	1.750	1.800	0.065	0.069	0.071
E	3.200	3.300	3.400	0.126	0.130	0.134
E1	-	-	-	-	-	-
E2	2.350	2.450	2.550	0.093	0.096	0.100
e	0.650 TYP			0.026		
H	0.35	0.450	0.550	0.014	0.018	0.022
L	0.35	0.450	0.550	0.014	0.018	0.022
L1	-	-	-	-	-	-
θ	-	-	-	-	-	-

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Q3 Tape and Reel Information



Note:

1. 10 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE +/-0.2
2. CAMBER NOT TO EXCEED 1mm IN 100mm, NONCUMULATIVE OVER 250mm
3. MATERIAL:BLACK STATIC DISSIPATIVE POLYSTYRENE
4. ALL DIMENSIONS ARE IN mm (UNLESS OTHERWISE SPECIFIED)
5. THICKNESS: 0.30 +/-0.05mm

Package Marking Information

Location:

1st Line

CSD = Fixed Characters

NNNNN = Product Code

2nd Line (Date Code)

YY = Last 2 digits of the Year

WW = 2-digit Work Week

C = Country of Origin

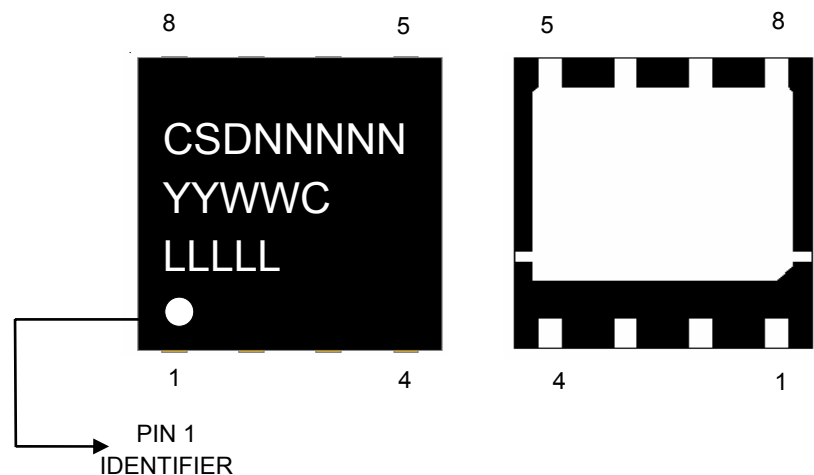
> Philippines = P

> Taiwan = T

> China = C

3rd Line

LLLLL = Last 5 digits of the Wafer Lot #



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